

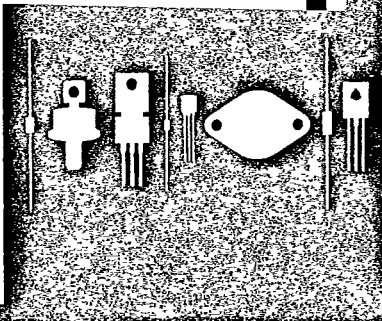
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145 Adams Avenue  
Hauppauge, New York 11788



MJ12005

NPN SILICON TRANSISTOR

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJ12005 type is a Silicon NPN Power Transistor mounted in a hermetically sealed metal case designed for Horizontal Deflection Circuits.

MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ )

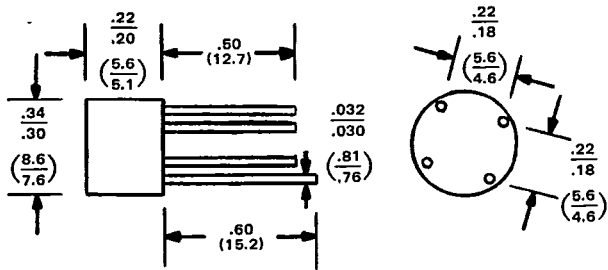
	SYMBOL		UNIT
Collector-Emitter Voltage	$V_{CE}$	1500	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current	$I_C$	8.0	A
Emitter Current	$I_E$	12	A
Base Current	$I_B$	4.0	A
Power Dissipation	$P_D$	100	W
Operating and Storage	$T_J, T_{STG}$	-65 TO +150	$^\circ\text{C}$
Junction Temperature	$\theta_{JC}$	1.25	$^\circ\text{C}/\text{W}$
Thermal Resistance			

ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
$I_{CES}$	$V_{CE}=1500\text{V}$		0.25	mA
$I_{EBO}$	$V_{BE}=5.0\text{V}$		0.1	mA
$BV_{CEO}$	$I_C=50\text{mA}$	750		V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		5.0	V
$V_{BE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		1.5	V
$t_f$	$I_C=5.0\text{A}, I_{B1}=1.0\text{A}, L_B=8.0\mu\text{H}$		1.0	$\mu\text{s}$
$I_{s/b}$	$V_{CE}=50\text{V}, t=1.0\text{s}$	2.0		A

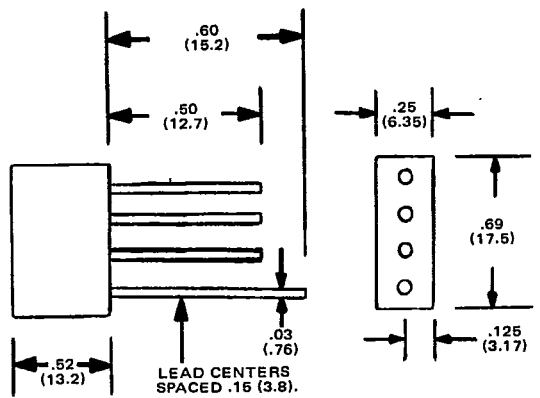
# CASE OUTLINE DRAWINGS

D



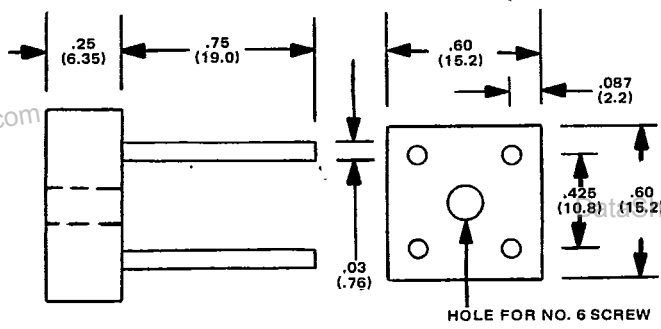
**CASE A**

*CBR1 Series*  
*CBR2 Series*



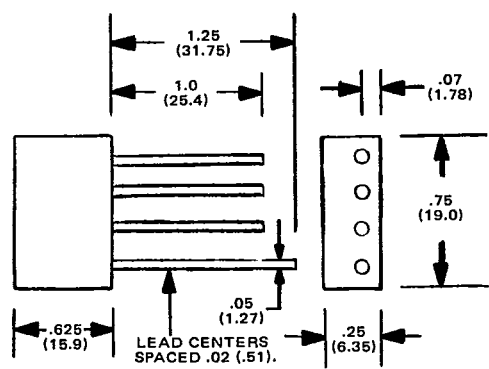
**CASE B**

*CBR1-L Series*  
*CBR2-L Series*



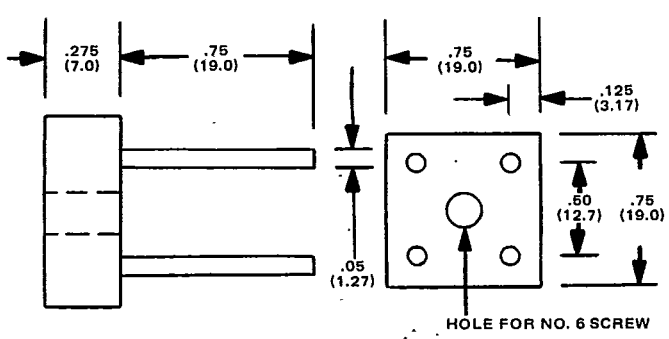
**CASE C**

*CBR3-P Series*



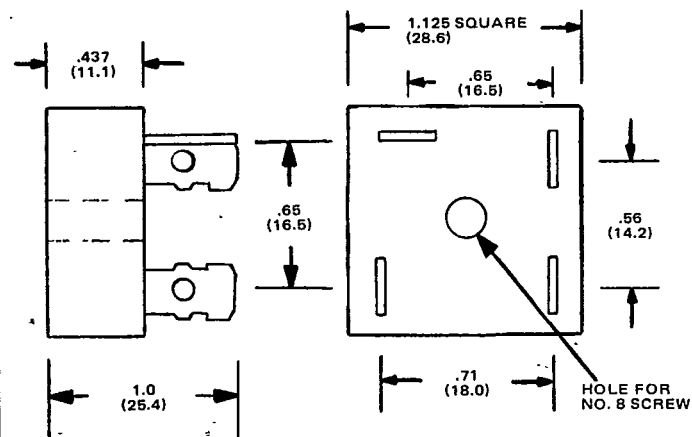
**CASE D**

*CBR4-L Series*



**CASE E**

*CBR8 Series*



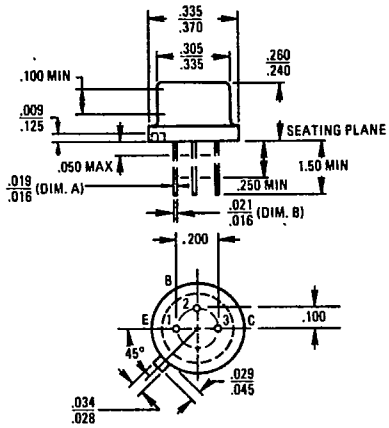
**CASE F**

*CBR10 Series, CBR25 Series*  
*CBR12 Series, CBR30 Series*

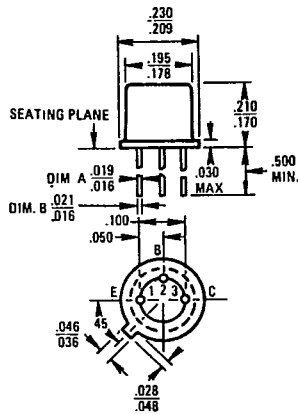
All Dimensions in Inches (Millimeters)

Drawings Not To Scale

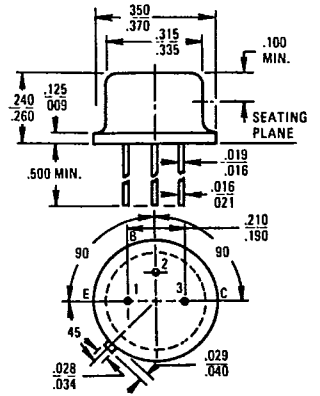
TO-5



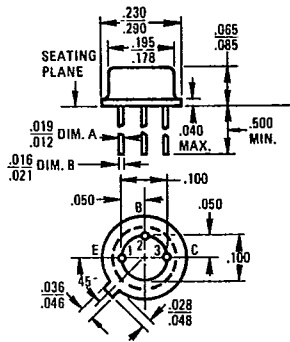
TO-18



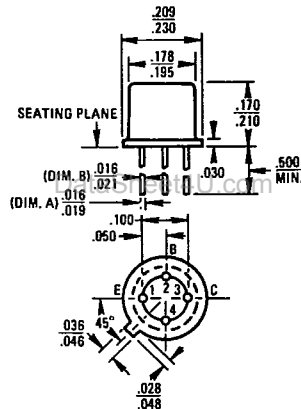
TO-39



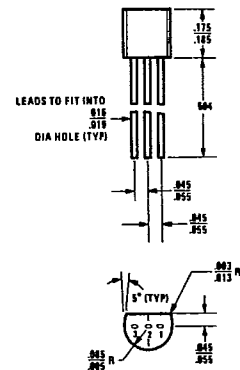
TO-46



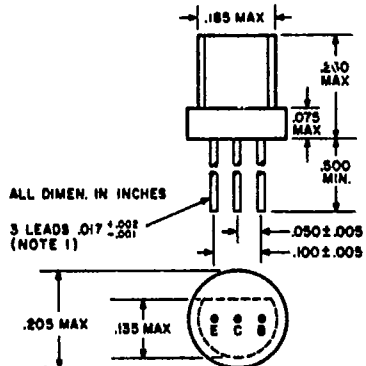
TO-72



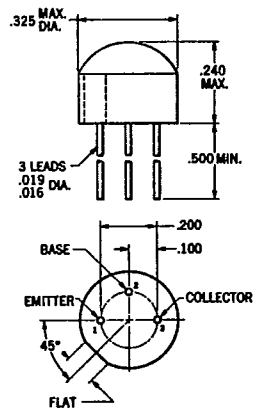
TO-92



TO-98



TO-105



TO-106

